

GaAs MMIC SP4T NON-REFLECTIVE SWITCH, DC - 2.0 GHz

Typical Applications

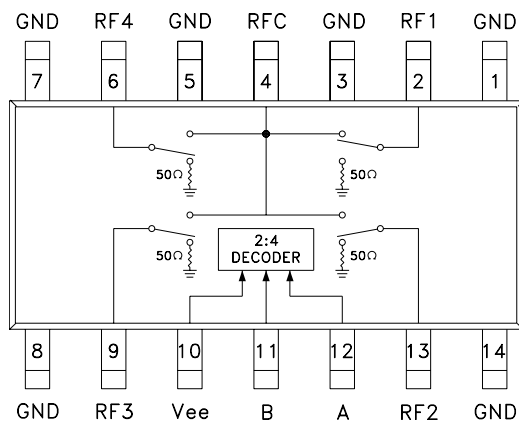
The HMC182S14 is ideal for:

- 800 - 1000 MHz Basestation

Features

- Low Insertion Loss: 0.8dB
- Integrated 2:4 Decoder
- 14 Lead SOIC Package

Functional Diagram



General Description

The HMC182S14 is a low-cost terminated SP4T switch in a 14-lead SOIC package for use in antenna diversity, switched filter banks, gain/attenuation selection, and general channel multiplexing applications. The switch can control signals up to 2 GHz. A 2:4 decoder is integrated on the switch, requiring only 2 control lines and a negative bias to select each RF path. The 2:4 decoder replaces 4 to 8 control lines normally required by GaAs SP4T switches. The HMC182S14 is a drop-in replacement for the HMC165S14 in applications requiring low “off state” VSWR. See positive bias/TTL SP4T HMC241QS16.

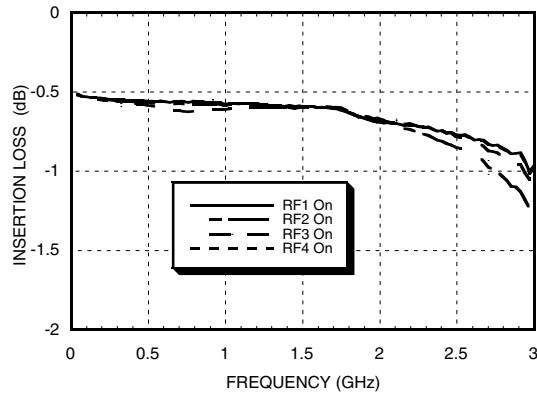
Electrical Specifications,

$T_A = +25^\circ C$, For 0/-5V Control and Vee = -5V in a 50 Ohm System

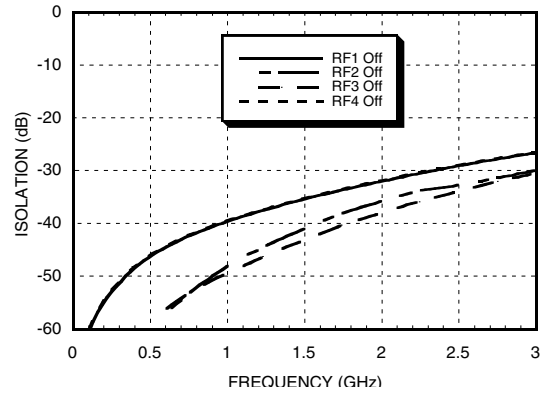
Parameter	Frequency	Min.	Typ.	Max.	Units
Insertion Loss	DC - 1.0 GHz		0.7	1.1	dB
	DC - 2.0 GHz		0.8	1.2	dB
Isolation	DC - 0.5 GHz	41	45		dB
	DC - 1.0 GHz	36	40		dB
	DC - 2.0 GHz	28	32		dB
Return Loss	“On State” DC - 1.0 GHz	21	25		dB
	“On State” DC - 2.0 GHz	16	20		dB
	“Off State” DC - 1.0 GHz	17	21		dB
	“Off State” DC - 2.0 GHz	13	17		dB
Input Power for 1 dB Compression	50 MHz		22		dBm
	0.5 - 2.0 GHz		24		dBm
Input Third Order Intercept (Two-Tone Input Power = 7 dBm Each Tone).	50 MHz	25	30		dBm
	0.5 - 1.0 GHz	41	45		dBm
	0.5 - 2.0 GHz	37	41		dBm
Switching Characteristics	DC - 2.0 GHz				
		tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)		25 50	ns ns

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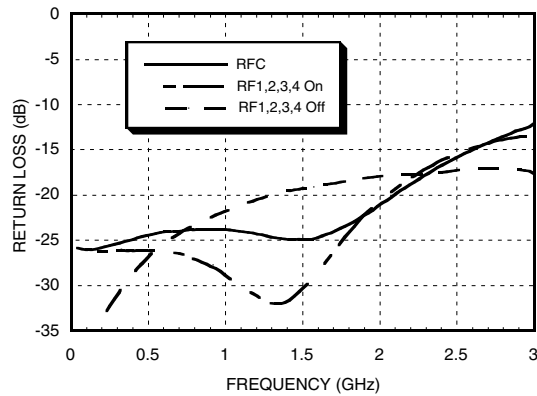
Insertion Loss



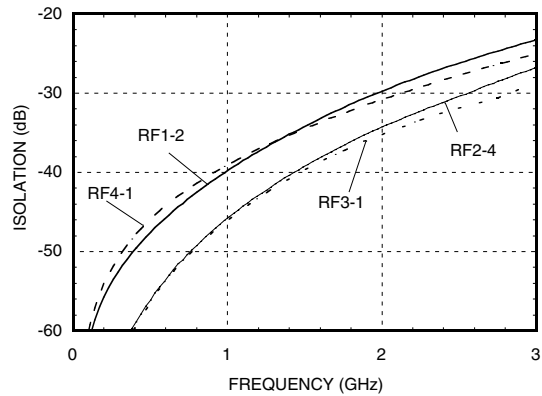
Isolation



Return Loss



Isolation Between Several RF I/Os



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Absolute Maximum Ratings

Bias Voltage Range (Port Vee)	-7.0 Vdc
Control Voltage Range (A & B)	Vee -0.5V to +1.0 Vdc
Channel Temperature	150 °C
Thermal Resistance (Insertion Loss Path)	123 °C/W
Thermal Resistance (Terminated Path)	260 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
Maximum Input Power	+27 dBm (<500 MHz) +30 dBm (>500 MHz)

Truth Table

Control Input		Signal Path State
A	B	RFCOM to:
High	High	RF1
Low	High	RF2
High	Low	RF3
Low	Low	RF4

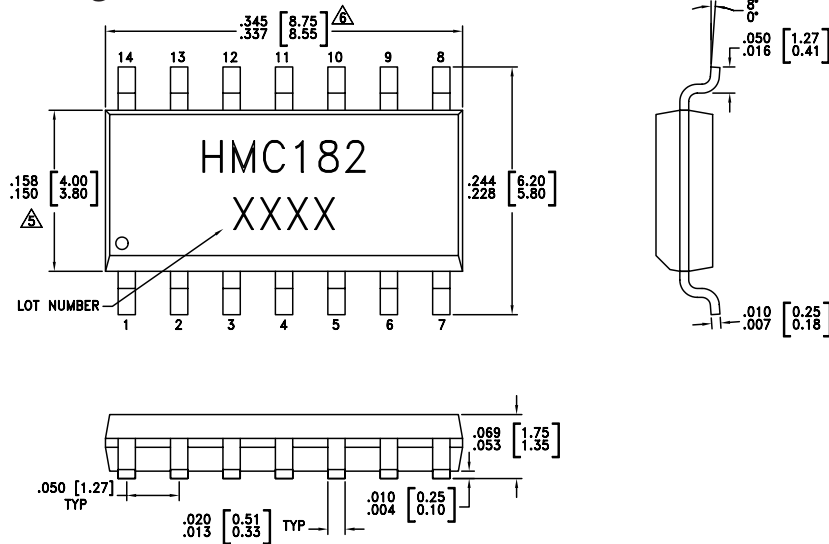
Control Voltages

State	Bias Condition
Low	0 to -3 VDC @ 70 uA Typ.
High	-5 to -4.2 VDC @ 5 uA Typ.

Bias Voltage & Current

Vee Range = -5.0 Vdc ± 10%		
Vee (Vdc)	Iee (Typ.) (mA)	Iee (Max.) (mA)
-5.0	4.0	7.0

Outline Drawing

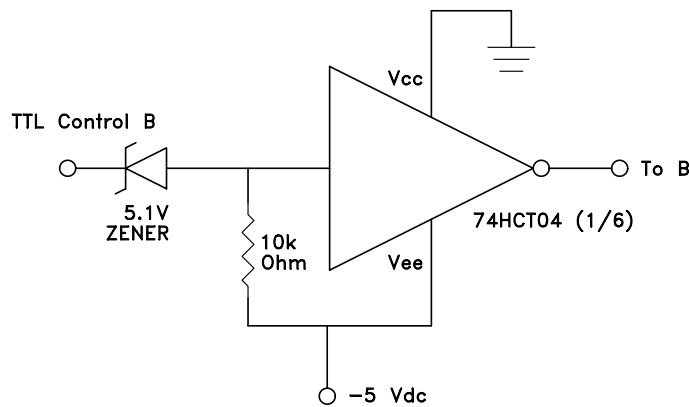
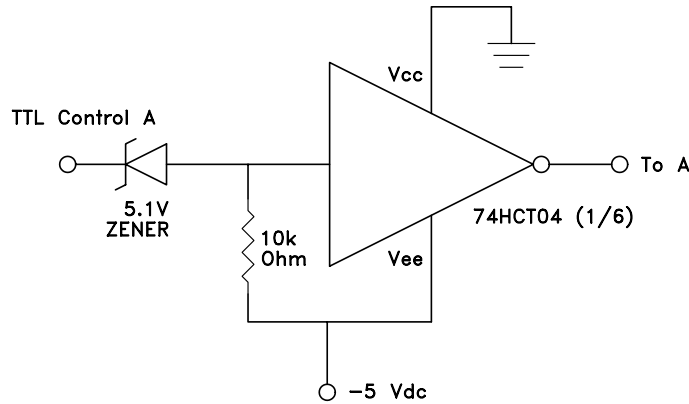


NOTES:

- PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
- LEADFRAME MATERIAL: COPPER ALLOY
- LEADFRAME PLATING: Sn/Pb SOLDER
- DIMENSIONS ARE IN INCHES [MILLIMETERS].
- Δ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- ∇ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

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TTL Interface Circuit

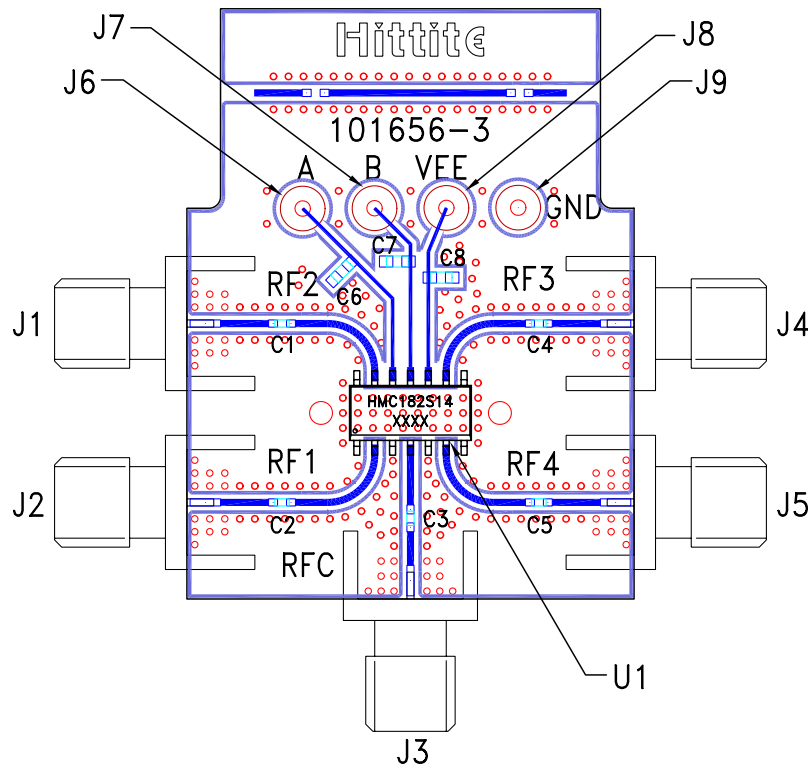


Note:

Control inputs A and B can be driven directly with TTL logic with -5 Volts applied to the HCT logic gate Vee pin and to Vee (pin 10) of the RF switch.

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Evaluation PCB



List of Material

Item	Description
J1 - J5	PC Mount SMA RF Connector
J6 - J9	DC Pin
C1 - C5	330 pF capacitor, 0402 Pkg.
C6 - C8	10,000 pF capacitor, 0603 Pkg.
U1	HMC182S14 SP4T Switch
PCB*	101656 Evaluation PCB

* Circuit Board Material: Rogers 4350

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

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Notes: